



## Description

### JMG P-channel Advanced Mode Power MOSFET

#### Features

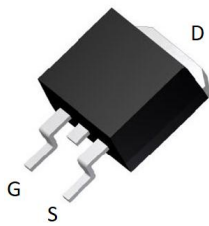
- 100V, -35A  
 $R_{DS(ON)} < 47m\Omega @ V_{GS} = -10V$   
 $R_{DS(ON)} < 57m\Omega @ V_{GS} = -4.5V$
- Advanced Split Gate Trench Technology
- Excellent  $R_{DS(ON)}$  and Low Gate Charge
- Lead free product is acquired

#### Application

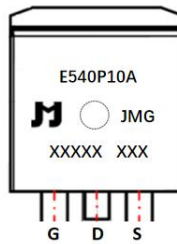
- Load Switch
- PWM Application
- Power management



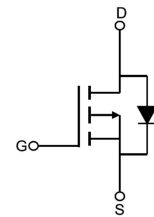
*100% UIS TESTED!*  
*100% ΔVds TESTED!*



TO-263-3L top view



Marking and pin Assignment



Schematic Diagram

## Package Marking and Ordering Information

Device Marking	Device	OUTLINE	Device Package	Reel Size	Reel (PCS)	Per Carton (PCS)
JMGE540P10A	JMGE540P10A	TAPING	TO-263-3L	13inch	800	4000

## Absolute Maximum Ratings (T<sub>C</sub>=25°C unless otherwise specified)

Symbol	Parameter	Max.	Units
V <sub>DSS</sub>	Drain-Source Voltage	-100	V
V <sub>GSS</sub>	Gate-Source Voltage	±20	V
I <sub>D</sub>	Continuous Drain Current	T <sub>C</sub> = 25°C	-35
		T <sub>C</sub> = 100°C	-23
I <sub>DM</sub>	Pulsed Drain Current <sup>note1</sup>	-140	A
E <sub>AS</sub>	Single Pulsed Avalanche Energy <sup>note2</sup>	90	mJ
P <sub>D</sub>	Power Dissipation	T <sub>C</sub> = 25°C	127
R <sub>θJC</sub>	Thermal Resistance, Junction to Case	1.2	°C/W
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range	-55 to +175	°C



## Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
<b>Off Characteristic</b>						
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =-250μA	-100	-	-	V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =-100V, V <sub>GS</sub> =0V,	-	-	-1.0	μA
I <sub>GSS</sub>	Gate to Body Leakage Current	V <sub>DS</sub> =0V, V <sub>GS</sub> = ±20V	-	-	±100	nA
<b>On Characteristics</b>						
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250μA	-1.0	-1.6	-2.5	V
R <sub>DS(on)</sub>	Static Drain-Source on-Resistance <small>note3</small>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-20A	-	36	47	mΩ
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-10A	-	41	57	
<b>Dynamic Characteristics</b>						
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =-50V, V <sub>GS</sub> =0V, f=1.0MHz	-	2120	-	pF
C <sub>oss</sub>	Output Capacitance		-	194	-	pF
C <sub>rss</sub>	Reverse Transfer Capacitance		-	13	-	pF
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> =-50V, I <sub>D</sub> =-5A, V <sub>GS</sub> =-10V	-	34	-	nC
Q <sub>gs</sub>	Gate-Source Charge		-	5	-	nC
Q <sub>gd</sub>	Gate-Drain("Miller") Charge		-	6	-	nC
<b>Switching Characteristics</b>						
t <sub>d(on)</sub>	Turn-on Delay Time	V <sub>DD</sub> =-50V, I <sub>D</sub> =-5A, R <sub>G</sub> =6Ω, V <sub>GS</sub> =-10V	-	9	-	ns
t <sub>r</sub>	Turn-on Rise Time		-	18	-	ns
t <sub>d(off)</sub>	Turn-off Delay Time		-	116	-	ns
t <sub>f</sub>	Turn-off Fall Time		-	152	-	ns
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
I <sub>S</sub>	Maximum Continuous Drain to Source Diode Forward Current		-	-	-35	A
I <sub>SM</sub>	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-140	A
V <sub>SD</sub>	Drain to Source Diode Forward Voltage	V <sub>GS</sub> =0V, I <sub>S</sub> =-30A	-	-	-1.2	V
t <sub>rr</sub>	Body Diode Reverse Recovery Time	T <sub>J</sub> =25°C, I <sub>F</sub> =-5A, dI/dt=100A/μs	-	48	-	ns
Q <sub>rr</sub>	Body Diode Reverse Recovery Charge		-	80	-	nC

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

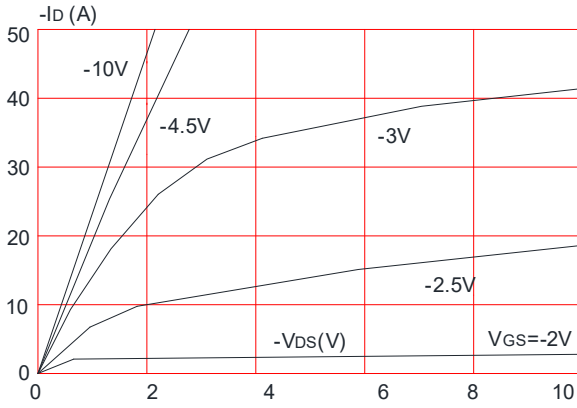
2. EAS condition: T<sub>J</sub>=25°C, V<sub>DD</sub>=-50V, V<sub>G</sub>=-10V, R<sub>G</sub>=25Ω, L=0.5mH, I<sub>AS</sub>=- 19A

3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%

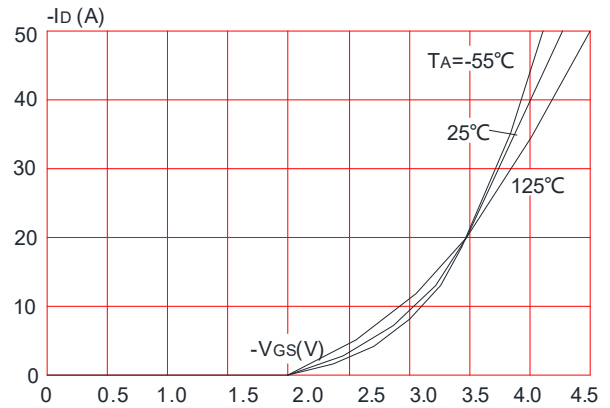


## Typical Performance Characteristics

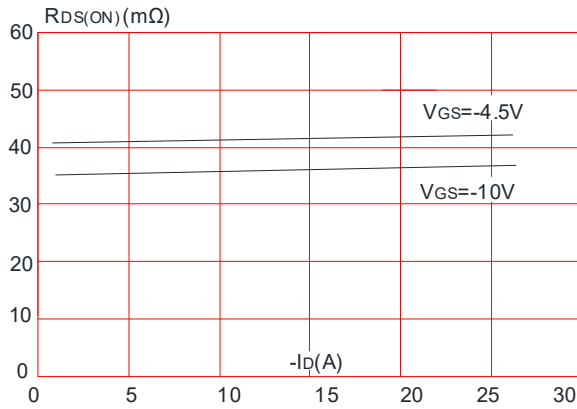
**Figure 1: Output Characteristics**



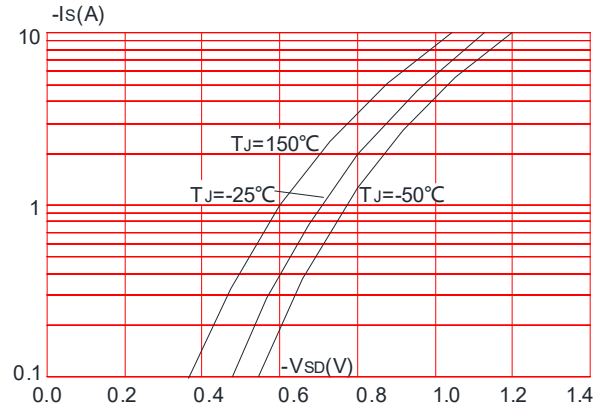
**Figure 2: Typical Transfer Characteristics**



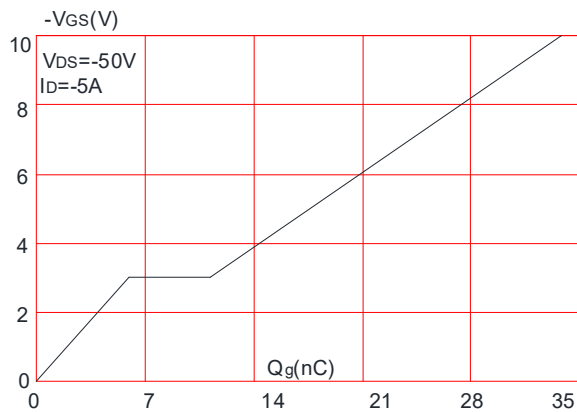
**Figure 3: On-resistance vs. Drain Current**



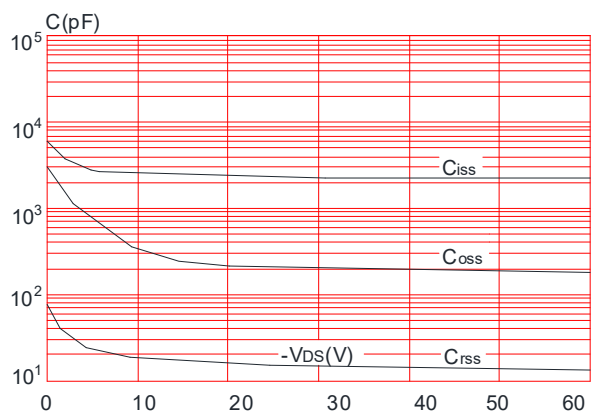
**Figure 4: Body Diode Characteristics**



**Figure 5: Gate Charge Characteristics**

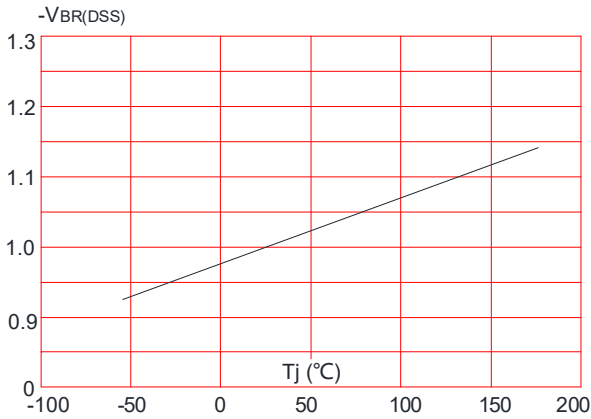


**Figure 6: Capacitance Characteristics**

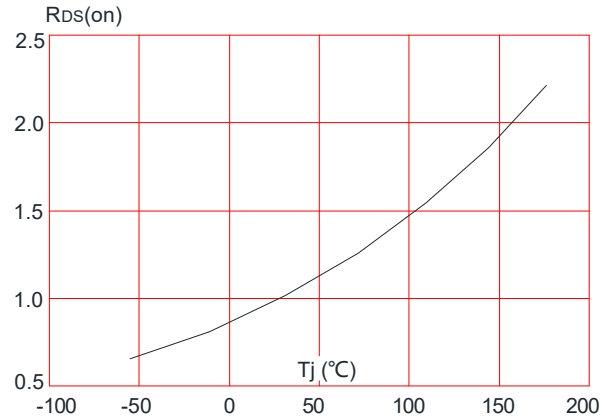




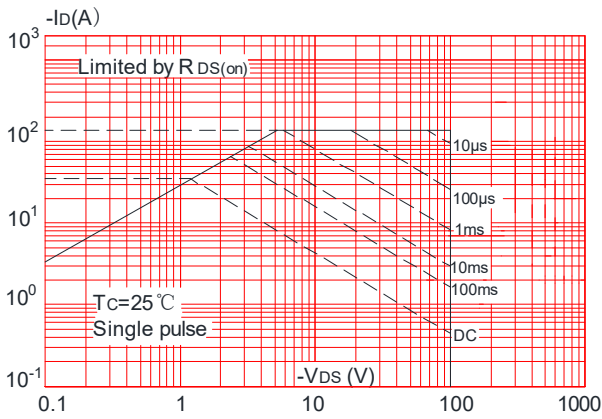
**Figure 7: Normalized Breakdown Voltage vs. Junction Temperature**



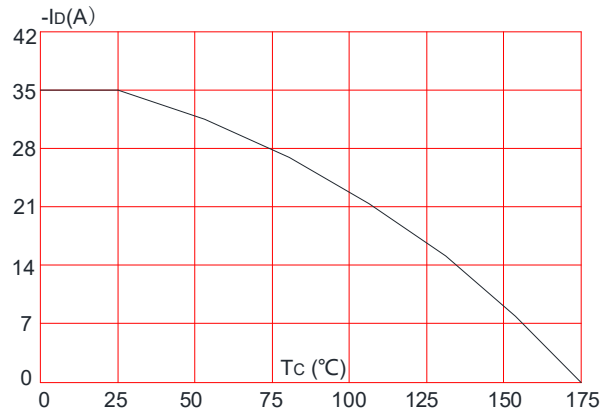
**Figure 8: Normalized on Resistance vs. Junction Temperature**



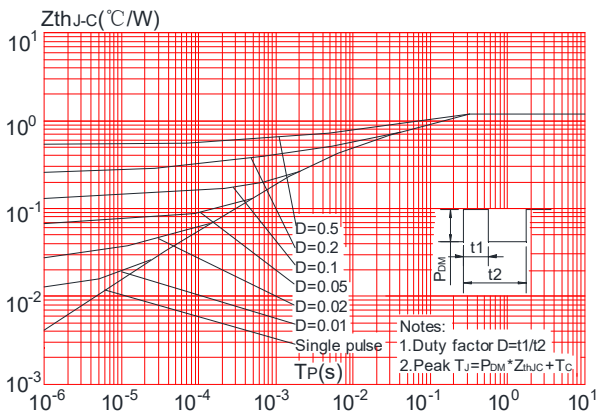
**Figure 9: Maximum Safe Operating Area**



**Figure 10: Maximum Continuous Drain Current vs. Case Temperature**



**Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case**



## Test Circuit

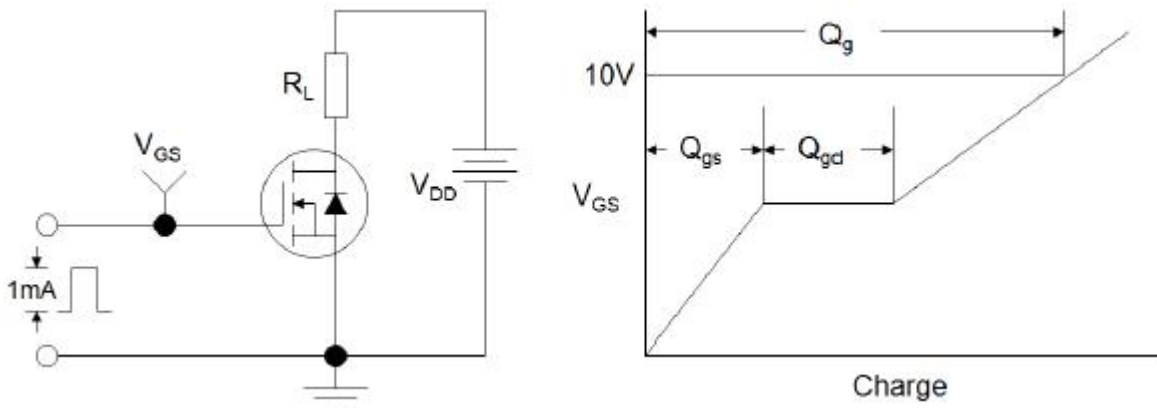


Figure1:Gate Charge Test Circuit & Waveform

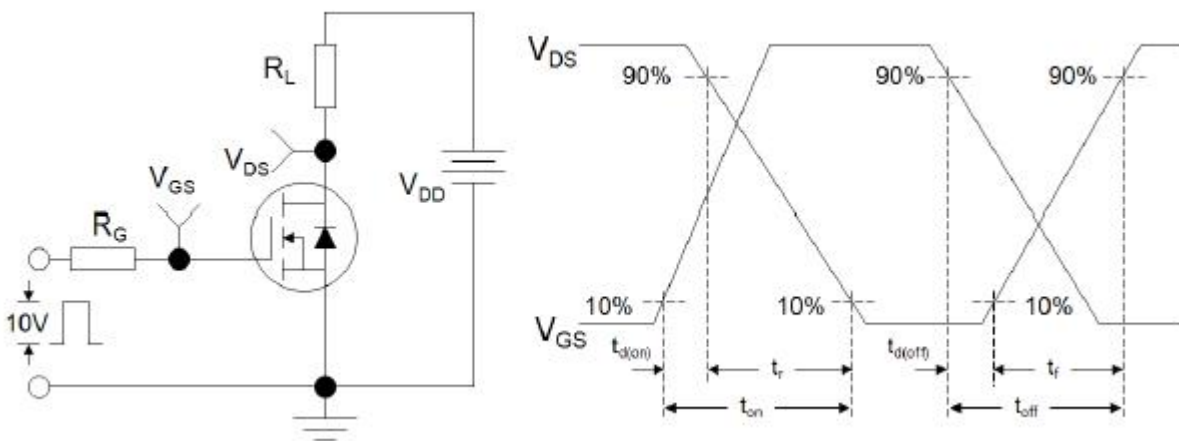


Figure 2: Resistive Switching Test Circuit & Waveforms

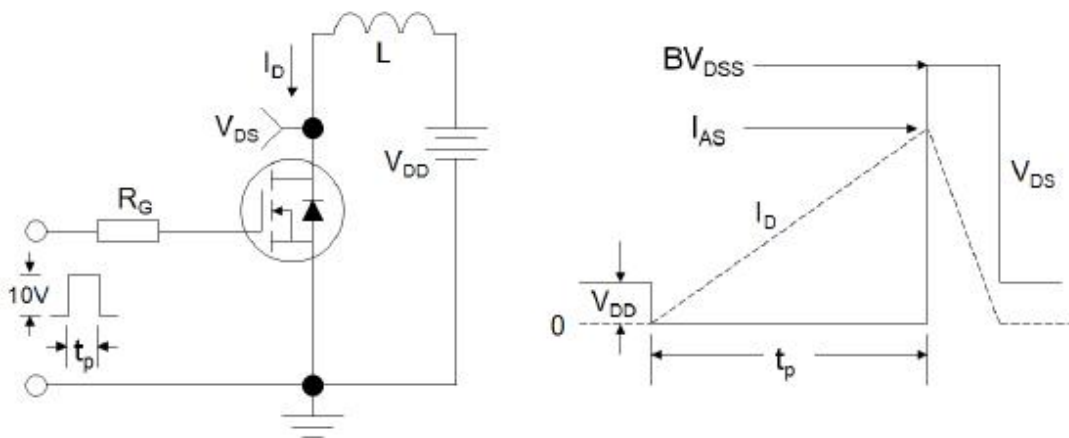
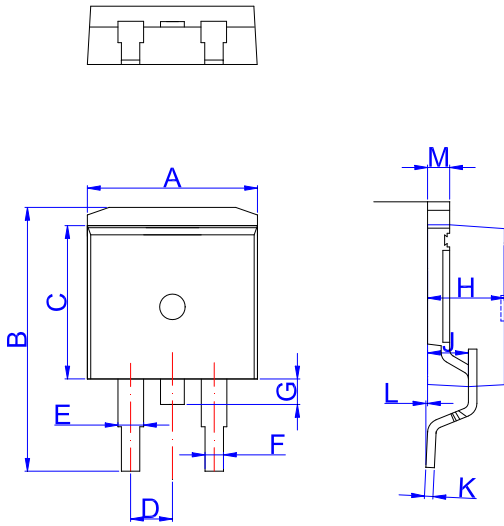


Figure 3:Unclamped Inductive Switching Test Circuit & Waveforms



## Package Mechanical Data-TO-263-3L



TO-263

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	9.90		10.20	0.390		0.402
B	14.70		15.80	0.579		0.622
C	9.4		9.6	0.37		0.378
D		2.54			0.100	
E	1.20		1.40	0.047		0.055
F	0.75		0.85	0.029		0.033
G			1.75			0.069
H	4.40		4.70	0.173		0.185
J	2.30		2.70	0.091		0.106
K	0.38		0.55	0.015		0.022
L	0	0.10	0.25	0	0.004	0.010
M	1.25		1.35	0.049		0.053

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